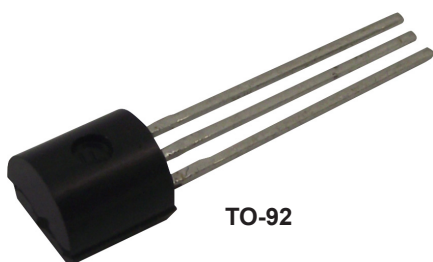


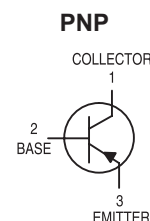
PNP Epitaxial Planar Silicon High Voltage Transistor, 150V_{CEO}, 600mA I_c

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TO-92

**RoHS
Compliant**



Absolute Max. Ratings T_A=25°C unless otherwise noted

Parameter	Symbol	Value	Units
Collector-Emitter Voltage	V _{CEO}	150	V
Collector-Base Voltage	V _{CB0}	160	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current Continuous	I _c	600	mA
Power Dissipation @T _A = 25°C Derate Above 25°C	P _D	625 5	mW mW/°C
Power Dissipation @T _c = 25°C Derate Above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-55 to +150	°C
Thermal Resistance			
Junction to Case	R _{th(j-c)}	83.3	°C/W
Junction to Ambient	R _{th(j-a)}	200	°C/W

Electrical Characteristics T_A = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Type	Max.	Units
Collector -Emitter Voltage	V _{CEO} *	I _c = 1mA, I _B = 0	150	-	-	V
Collector -Base Voltage	V _{CB0}	I _c = 100µA, I _E = 0	160	-	-	V
Emitter -Base Voltage	V _{EB0}	I _E = 10µA, I _c = 0	5	-	-	V
Collector-Cut off Current	I _{CB0}	V _{CB} = 160V, I _E = 0	-	-	50	nA
Emitter Cut-off Current	I _{EB0}	T _A = 100°C V _{CB} = 160V, I _E = 0 V _{EB} = 4V, I _c = 0	- -	- -	50 50	µA nA
DC Current Gain	h _{FE} *	I _c = 1mA, V _{CE} = 5V I _c = 10mA, V _{CE} = 5V I _c = 50mA, V _{CE} = 5V	50 60 50	- - -	- 240 -	
Collector Emitter Saturation Voltage	V _{CE(sat)} *	I _c = 10mA, I _B = 1mA I _c = 50mA, I _B = 5mA	- -	- -	0.2 0.5	V
Base Emitter Saturation Voltage	V _{BE(sat)} *	I _c = 10mA, I _B = 1mA I _c = 50mA, I _B = 5mA	- -	- -	1.0 1.0	V

*Pulse Test: Pulse Width = 300µs, Duty Cycle = 2% T

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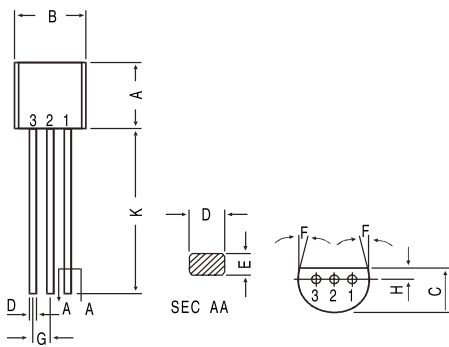
PNP Epitaxial Planar Silicon High Voltage Transistor, 150V_{CEO}, 600mA I_c



Dynamic Characteristics

Parameter	Symbol	Test Condition	Min.	Type	Max.	Units
Small Signal Current Gain	hfe	I _c = 1mA, V _{CE} = 10V, f = 1kHz	40	-	200	
Transition Frequency	f _t	V _{CE} = 10V, I _c = 10mA, f = 100MHz	100	-	300	MHz
Output Capacitance	C _{obo}	V _{CB} = 10V, I _E = 0, f = 1MHz	-	-	6	pF
Noise Figure	NF	V _{CE} = 5V, I _c = 250μA R = 1kΩ, f = 10Hz to 15.7kHz	-	-	8	dB

TO-92 Plastic Package



PIN CONFIGURATION
 1. COLLECTOR
 2. BASE
 3. EMITTER

Dim.	Min.	Max.
A	4.32	5.33
B	4.45	5.2
C	3.18	4.19
D	0.41	0.55
E	0.35	0.5
F	5 Deg.	
G	1.14	1.4
H	1.14	1.53
K	12.7	-

Dimensions : Millimetres

Part Number Table

Description	Part Number
PNP Epitaxial Planar Silicon High Voltage Transistor, 150V, 600mA, TO-92	2N5401

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